

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

5 a first base material which is provided at least one semiconductor device mounted on one main surface of the first base material, a plurality of first connection portions provided on the main surface of the first base material on the side on which the semiconductor device is mounted and being electrically connected to the semiconductor device, and a plurality of second connection portions provided outside a region on which the semiconductor device is mounted on the main surface of the first base material on the side on which the semiconductor device is mounted; and

15 a second base material which is disposed facing the main surface of the first base material on a side opposite to the side on which the semiconductor device is mounted, bonded to an edge of the first base material so that the first base material is mounted on the second base material, and provided a plurality of third connection portions provided outside a region on which the first base material is mounted on the main surface of the second base material on the side facing the first base material and being electrically connected to at least one of the second connection portions.

20 2. The device according to claim 1, wherein:
25 the region of the first base material on the

opposite side of the region on which the semiconductor device is mounted is provided apart from the second base material.

3. The device according to claim 1, wherein:

5 the region of the first base material on the opposite side of the region on which the semiconductor device is mounted, is bonded to the second base material by an adhesive material having an elasticity of 3.2 MPa or less.

10 4. The device according to claim 1, wherein:

 the semiconductor device has a thickness of 0.15 mm or less.

5. The device according to claim 1, wherein:

 the second connection portion connected to the
15 third connection portion among the respective second connection portions is provided outside the other second connection portions.

6. The device according to claim 1, further comprising:

20 a conductive layer comprising at least one layer or a solder ball, provided on the second connection portion other than the second connection portion connected to the third connection portion among the respective second connection portions.

25 7. The device according to claim 1, wherein:

 the semiconductor device is flip-chip or wire-bonding connected to the first connection portions and

mounted on the first base material.

8. The device according to claim 1, wherein:

the first base material is a one-sided wiring substrate which is provided the respective first connection portions and the respective second connection portions only on the side of the first base material on which the semiconductor device is mounted.

9. The device according to claim 1, wherein:

the first base material is bonded to the second base material by an adhesive material, which comprising a material from which hardness is obtained so as to be capable of electrically and appropriately connecting the respective second connection portions to the third connection portions by a wire bonding method and holding the first base material apart from the second base material, and provided on an edge of the main surface of the first base material on a side opposite to the side on which the semiconductor device is mounted.

10. The device according to claim 1, further comprising:

at least one electric component other than the semiconductor device, mounted on the main surface of the second base material on a side opposite to the side on which the first base material is mounted.

11. A manufacturing method for a semiconductor device, comprising:

disposing a first base material and a second base material in such a manner that the first and second base materials face each other, the first base material is provided at least one semiconductor device mounted on one main surface of the first base material, the first base material is provided a plurality of first connection portions provided on the main surface of the first base material on a side on which the semiconductor device is mounted and being electrically connected to the semiconductor device, and the first base material is provided a plurality of second connection portions provided outside a region on which the semiconductor device is mounted on the main surface of the first base material on the side on which the semiconductor device is mounted, and the second base material being disposed facing the main surface of the first base material on a side opposite to the side on which the semiconductor device is mounted, and the second base material including a plurality of third connection portions provided outside a region on which the first base material is mounted on the main surface of the second base material on the side facing the first base material and being electrically connected to at least one of the second connection portions, and

mounting the first base material on the second base material, by bonding an edge of the first base

material to the second base material.

12. The method according to claim 11, wherein:

the region of the first base material on the opposite side of the region on which the semiconductor device is mounted is provided apart from the second base material.

13. The method according to claim 11, wherein:

the region of the first base material on the opposite side of the region on which the semiconductor device is mounted, is bonded to the second base material by an adhesive material having an elasticity of 3.2 MPa or less.

14. The method according to claim 11, wherein:

a semiconductor device having a thickness of 0.15 mm or less is used as the semiconductor device.

15. The method according to claim 11, wherein:

the second connection portion connected to the third connection portion among the respective second connection portions is provided outside the other second connection portions.

16. The device according to claim 11, further comprising:

providing a conductive layer comprising at least one layer or a solder ball on the second connection portion other than the second connection portion connected to the third connection portion among the respective second connection portions.

17. The method according to claim 11, wherein:

the semiconductor device is connected to the first connection portions and mounted on the first base material by a flip-chip connection method or a wire-bonding method.

18. The method according to claim 11, wherein:

a one-sided wiring substrate provided the respective first connection portions and the respective second connection portions only on the side of the first base material on which the semiconductor device is mounted is used as the first base material.

19. The method according to claim 11, wherein:

the first base material is bonded to the second base material by an adhesive material, which comprising a material from which hardness is obtained so as to be capable of electrically and appropriately connecting the respective second connection portions to the third connection portions by a wire bonding method and holding the first base material apart from the second base material, and provided on an edge of the main surface of the first base material on a side opposite to the side on which the semiconductor device is mounted.

20. The method according to claim 11, further comprising:

mounting at least one electric component other than the semiconductor device on the main surface of

the second base material on a side opposite to the side on which the first base material is mounted.